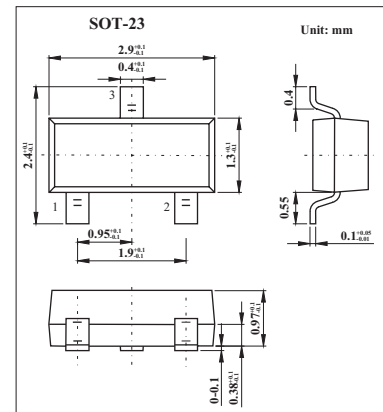


Schottky Barrier Diode

1SS365

■ Features

- Small-sized package facilitates high-density mounting and permits 1SS365-applied equipment to be made smaller.
- Small interterminal capacitance.
- Low forward voltage.
- High breakdown voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Value | Unit |
|----------------------|-----------|-------------|------------------|
| Reverse Voltage | V_R | 10 | V |
| Forward Current | I_F | 35 | mA |
| Junction Temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---------------------------|------------|---------------------------------------|-----|-----|------|----------------|
| Forward Voltage | $V_{F(1)}$ | $I_F = 1\text{ mA}$ | 350 | | 420 | mV |
| | $V_{F(2)}$ | $I_F = 10\text{ mA}$ | 480 | | 580 | mV |
| Forward Current | I_F | $V_F = 1\text{ V}$ | 35 | | | mA |
| Reverse Current | $I_{R(1)}$ | $V_R = 2\text{ V}$ | | | 0.2 | $\mu\text{ A}$ |
| | $I_{R(2)}$ | $V_R = 10\text{ V}$ | | | 10 | $\mu\text{ A}$ |
| Interterminal Capacitance | C | $V_R = 10\text{ V}, f = 1\text{ MHz}$ | | | 0.85 | pF |

■ Marking

| | |
|---------|----|
| Marking | EH |
|---------|----|